

• General Description

It combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$.

• Features

- Low $R_{DS(ON)}$ to minimize conductive loss
- Low Gate Charge for fast switching
- Low Thermal resistance

• Application

- BLDC Motor driver
- DC-DC
- Load Switch

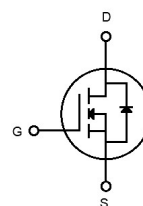
• Ordering Information:

Part NO.	ZMS011N06HB6
Marking	ZMS011N06H
Packing Information	REEL TAPE
Basic ordering unit (pcs)	800

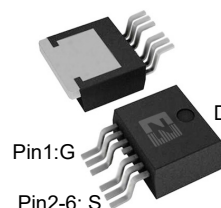
• Absolute Maximum Ratings ($T_C=25^{\circ}C$)

Parameter	Symbol	Conditions	Value	Unit
Drain-Source Voltage	V_{DS}		60	V
Gate-Source Voltage	V_{GS}		± 20	V
Continuous Drain Current	I_D	$T_C=25^{\circ}C$	260	A
	I_D	$T_C=75^{\circ}C$	213	A
	I_D	$T_C=100^{\circ}C$	184	A
Pulsed Drain Current	I_{DM}	Pulsed; $t_p \leq 10 \mu s$; $T_{mb} = 25^{\circ}C$;	780	A
Total Power Dissipation	P_D	$T_C=25^{\circ}C$	214	W
Total Power Dissipation	P_D	$T_A=25^{\circ}C$	5.0	W
Operating Junction Temperature	T_J		-55 to +175	$^{\circ}C$
Storage Temperature	T_{STG}		-55 to +175	$^{\circ}C$
Single Pulse Avalanche Energy	E_{AS}	$L=0.1mH, V_{GS}=10V, R_g=25\Omega,$	240	mJ
		$L=0.5mH, V_{GS}=10V, R_g=25\Omega,$	552	mJ
ESD Level (HBM)	CLASS 2			

• Product Summary



$V_{DS} = 60V$
 $R_{DS(ON)} = 1.1m\Omega$
 $I_D = 260A$



TO-263-6



•Thermal resistance

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	R_{thJC}		-	0.7	°C/W
Thermal resistance, junction-ambient	$R_{thJA}^{①}$		-	30	°C/W
Soldering temperature	T_{sold}		-	260	°C

•Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	60			V
Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS}=V_{DS}, I_D=250\mu A$	2.0	2.7	4.0	V
Drain-Source Leakage Current	I_{DSS}	$V_{GS}=0V, V_{DS}=60V$			1.0	μA
Gate- Source Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$			100	nA
Static Drain-source On Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=55A$		1.1	1.5	m Ω
Forward Transconductance	g_{FS}	$V_{DS}=5V, I_{SD}=10A$		45		S
Diode Forward Voltage	V_{FSD}	$V_{GS}=0V, I_{SD}=55A$			1.3	V

•Dynamic characteristics

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Input capacitance	C_{iss}	$f=1MHz, V_{DS}=25V$	-	7650	-	pF
Output capacitance	C_{oss}		-	4430	-	
Reverse transfer capacitance	C_{rss}		-	572	-	
Gate Resistance	R_g	$f=1MHz$	-	1.6		Ω
Total gate charge	Q_g	$V_{DD}=15V, I_D=55A, V_{GS}=10V$	-	142	-	nC
Gate - Source charge	Q_{gs}		-	42	-	
Gate - Drain charge	Q_{gd}		-	29	-	
Turn-ON Delay time	$t_{D(on)}$	$V_{GS}=10V, V_{DS}=15V, R_G=3.3\Omega, I_D=20A$	-	30	-	ns
Turn-ON Rise time	t_r		-	12	-	ns
Turn-Off Delay time	$t_{D(off)}$		-	65	-	ns
Turn-Off Fall time	t_f		-	14	-	ns
Reverse Recovery Time	t_{rr}	$V_{DD}=20V, di_s/dt=100A/\mu s, I_S=50A$	-	210	-	ns
Reverse Recovery Charge	Q_{rr}		-	200	-	nC

Fig.1 Gate-Charge Characteristics

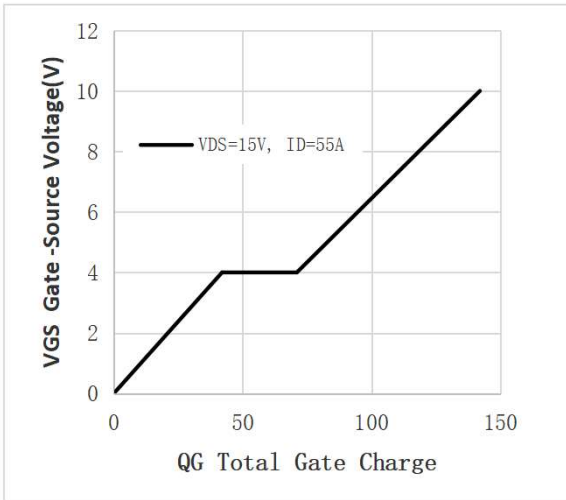


Fig.2 Capacitance Characteristics

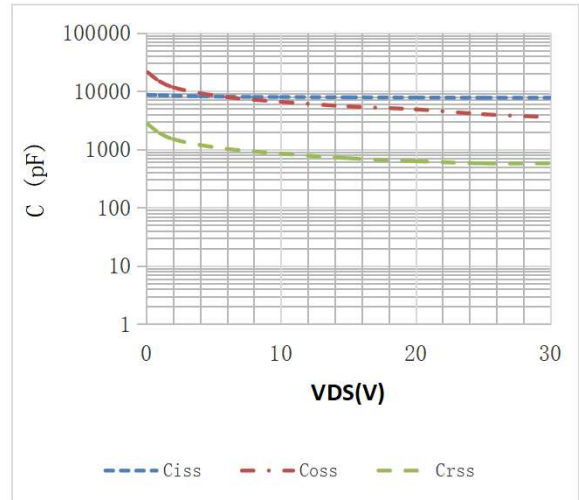


Fig.3 Power Dissipation

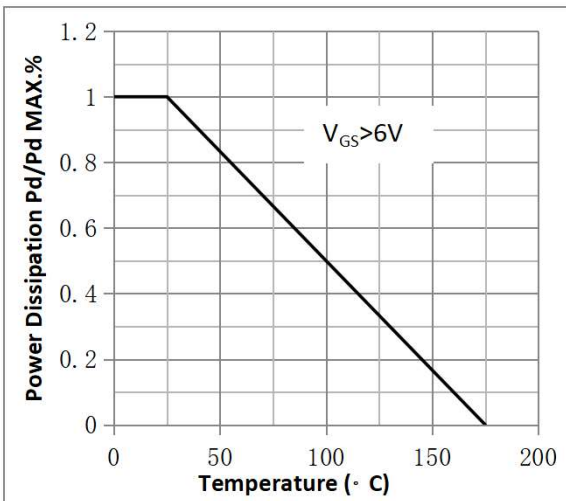


Fig.4 Typical output Characteristics

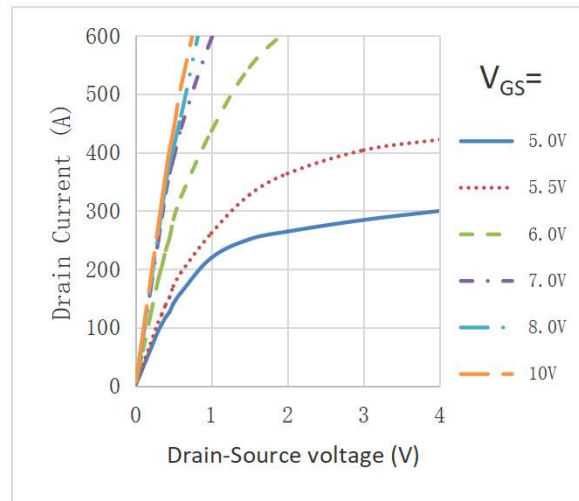


Fig.5 Threshold Voltage V.S Junction Temperature

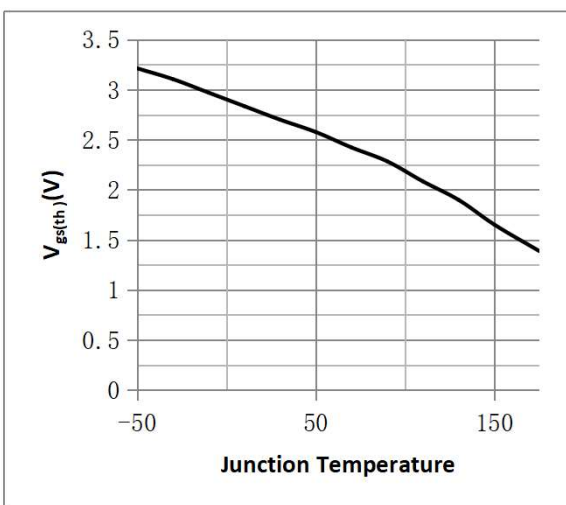


Fig.6 Resistance V.S Drain Current

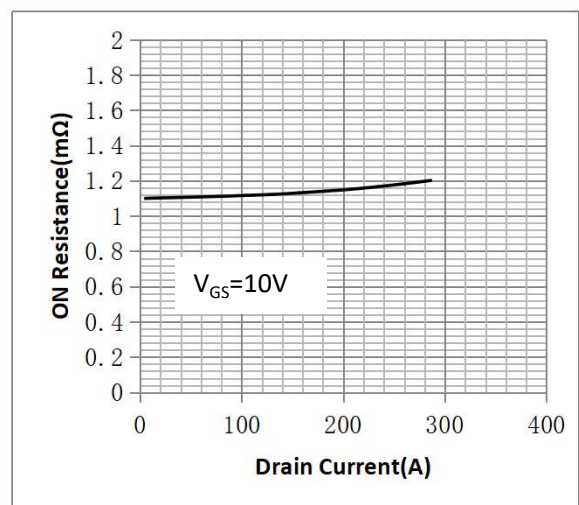


Fig.7 On-Resistance VS Gate Source Voltage

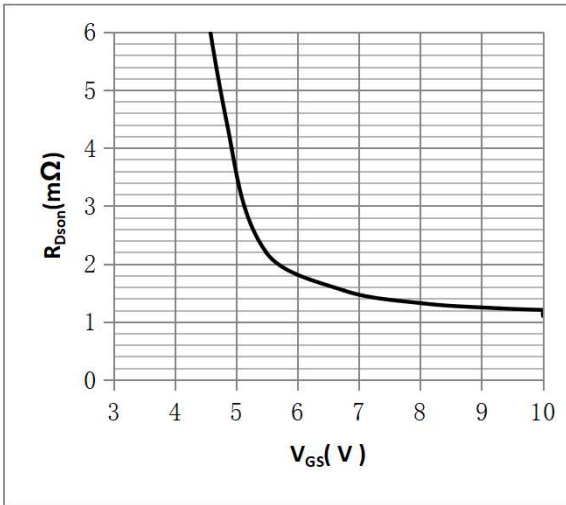


Fig.8 On-Resistance V.S Junction Temperature

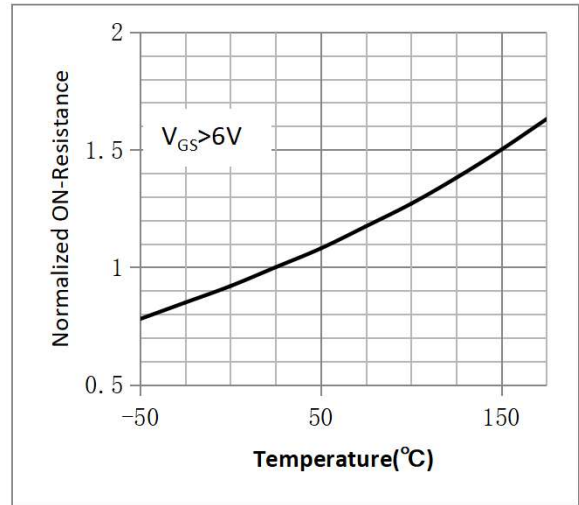


Figure 9. Diode Forward Voltage vs. Current

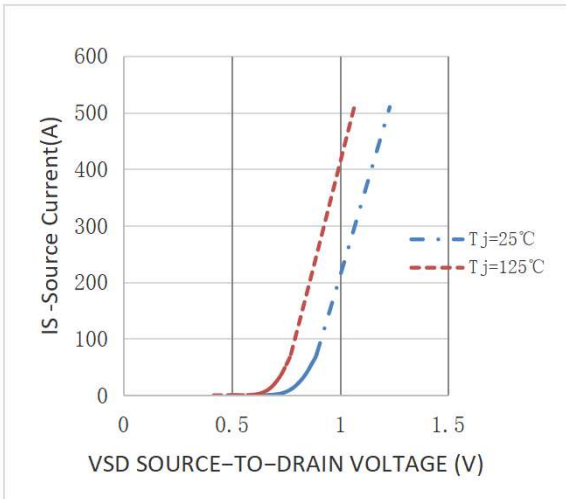


Figure 10. Transfer Characteristics

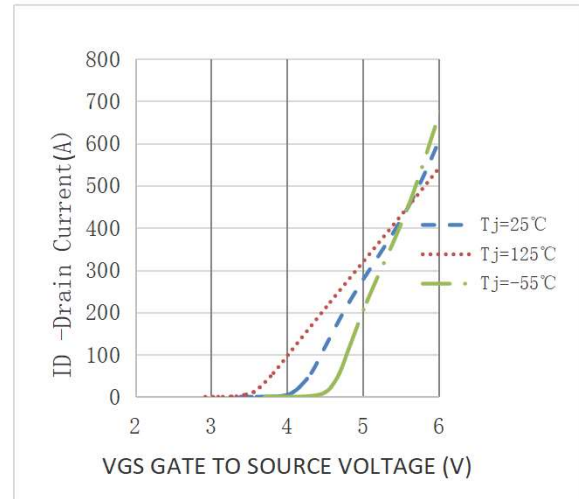


Fig.11 Safe Operating Area

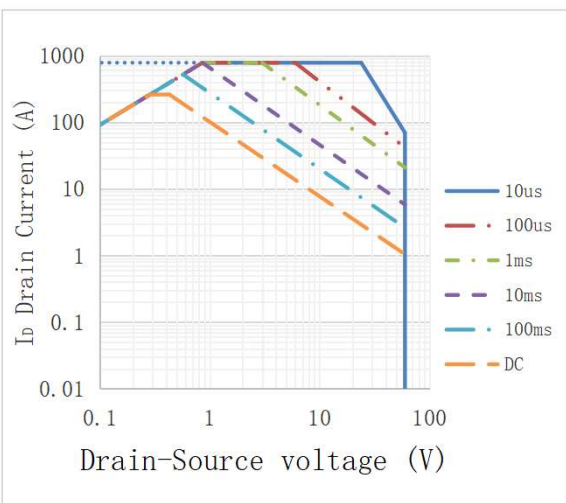
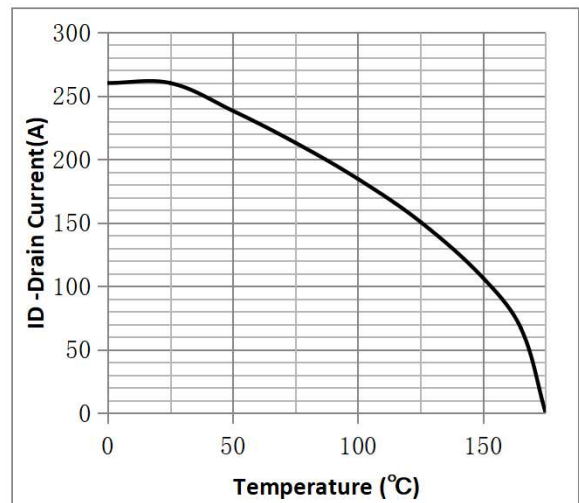
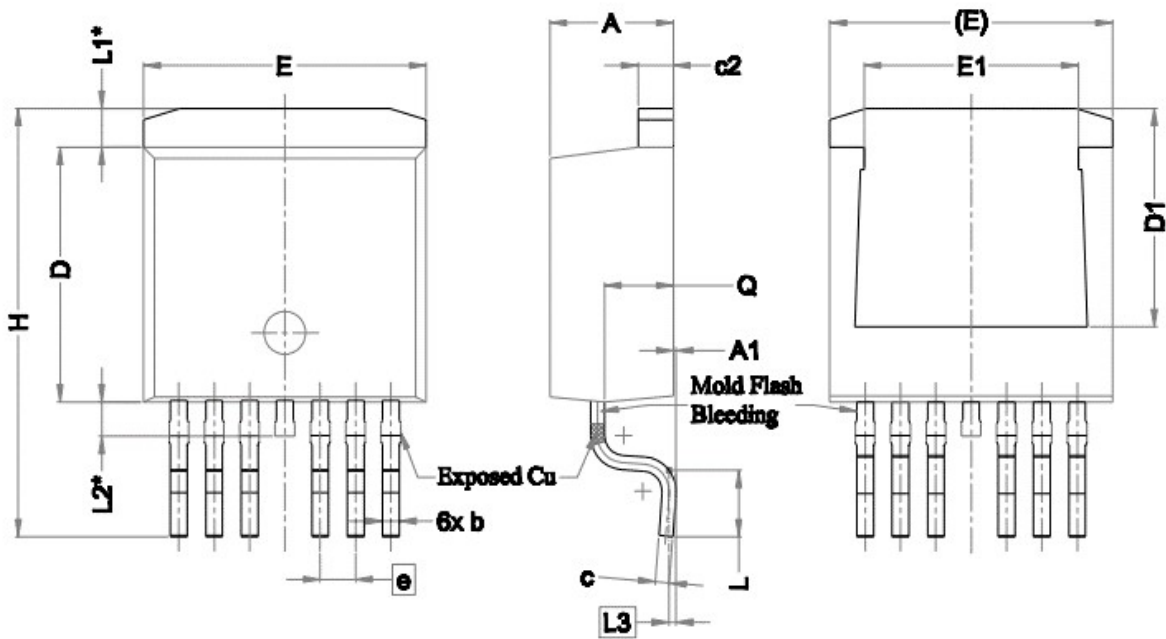


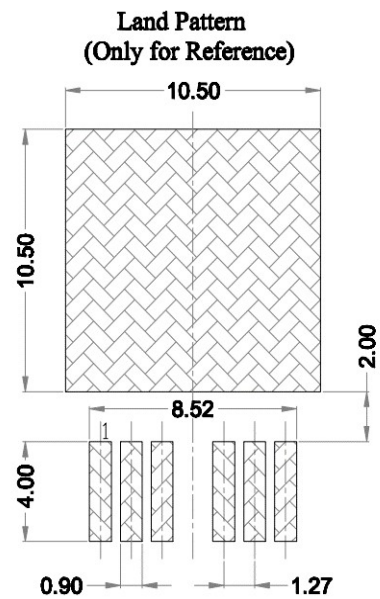
Fig.12 ID vs. Case Temperature^②



•TO-263-6 Package Outline



SYMBOL	DIMENSIONS		
	MIN.	NOM.	MAX.
A	4.24	4.44	4.64
A1	0.00	0.10	0.25
b	0.50	0.60	0.70
c	0.40	0.50	0.60
c2	1.15	1.27	1.40
D	8.82	8.92	9.02
D1	6.86	7.65	—
E	9.96	10.16	10.36
E1	6.89	7.77	7.89
e	1.27 BSC		
H	14.61	15.00	15.88
L	1.78	2.32	2.79
L1	1.36 REF.		
L2	1.20 REF.		
L3	0.25 BSC		
Q	2.30	2.48	2.70



Note:

- ① Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate;
- ② Practically the current will be limited by PCB, thermal design and operating temperature. VGS=10V.

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Revision History

Version	Date	Change
A	2021.12.6	
B	2022.9.5	1.Add Reach,HF figure,2.ID curve modify
C	2023.12.28	Correct SOA